

Notice of References Cited	Application/Control No. 09/832,933	Applicant(s)/Patent Under Reexamination WU ET AL.	
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U.S. PATENT DOCUMENTS

*		Document Number Country Code-Number-Kind Code	Date MM-YYYY	Name	Classification
	A	US-6,278,964	08-2001	Fang et al.	703/19
	B	US-			
	C	US-			
	D	US-			
	E	US-			
	F	US-			
	G	US-			
	H	US-			
	I	US-			
	J	US-			
	K	US-			
	L	US-			
	M	US-			

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NON-PATENT DOCUMENTS

*		Include as applicable: Author, Title Date, Publisher, Edition or Volume, Pertinent Pages)
	U	Le et al., "Digital Test Circuit and Optimization for AC Hot-Carrier Reliability Characterization and Model Calibration under Realistic High Frequency Stress Conditions" IEEE 1997. pg. 56-62.
	V	Takeda-E., "An Empirical Model for Device Degradation Due to Hot-Carrier Injection" IEEE 1983. pg. 111-113.
	W	Wu et al., "GLACIER: A Hot Carrier Gate Level Circuit Characterization Simulation System for VLSI Design" 2000 March. IEEE pg. 73-79.
	X	Aur et al., "Circuit Hot Electron Effect Simulation" 1987 Texas Instrument. pg. 498-501.

*A copy of this reference is not being furnished with this Office action. (See MPEP § 707.05(a).)
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	V	Chen et al., "Statistical Variation of NMOSFET Hot Carrier Lifetime and its Impact on Digital Circuit Reliability" IEEE. pg.29-32. 1995.
	W	Jiang et al., "Key Hot-Carrier Degradation Model Calibration and Verification Issues for Accurate AC Circuit-Level Reliability Simulation". IEEE 1997. pg.300-306.
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